

**ABSTRACT OF THE DISCLOSURE**

A semiconductor light-emitting device has first and second semiconductor layers each of a first conductivity type, a third semiconductor layer of a second conductivity type  
5 provided between the first and second semiconductor layers, and an active layer provided between the second and third semiconductor layers to emit light with charge injected therein from the second and third semiconductor layers. A graded composition layer is provided between the active layer  
10 and the third semiconductor layer to have a varying composition which is nearly equal to the composition of the active layer at the interface with the active layer and to the composition of the third semiconductor layer at the interface with the third semiconductor layer.

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